NOT RECOMMENDED FOR NEW DESIGN
USE DMN2451UFDQ

Lead-free Green

DMN2400UFDQ

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
20V	0.6Ω @ V_{GS} = 4.5V	0.9A
	0.8Ω @ V_{GS} = 2.5V	0.7A
	1.0Ω @ V_{GS} = 1.8V	0.5A
	1.6Ω @ V_{GS} = 1.5V	0.3A

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max.
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN2400UFDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

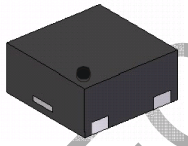
- Power management functions
- Battery operated systems and solid-state relays
- Load switches

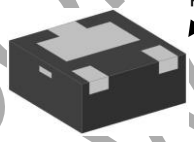
Mechanical Data

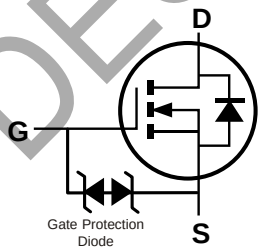
- Package: U-DFN1212-3
- Package Material: Molded Plastic;
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe;
  Solderable per MIL-STD-202, Method 208 e4
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)


ESD PROTECTED

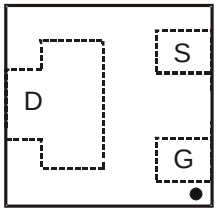
U-DFN1212-3 (Type C)


Top View


Bottom View



Equivalent Circuit



Pin-Out Top View

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN2400UFDQ-7	U-DFN1212-3 (Type C)	3,000	Tape & Reel
DMN2400UFDQ-13	U-DFN1212-3 (Type C)	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

K24 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: J = 2022)
M = Month (ex: 9 = September)

Date Code Key

Year	2015	…	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	C	…	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.9 0.7	A
Continuous Drain Current (Note 6) V_{GS} = 2.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.7 0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	3.0	A
Maximum Body Diode Forward Current (Note 6)			I_S	0.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.44	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	283	°C/W
Total Power Dissipation (Note 6)		P_D	0.85	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	147	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta Jc}$	112	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	80 100	nA	V_{DS} = 4.5V, V_{GS} = 0V V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	-	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.35	0.6	Ω	V_{GS} = 4.5V, I_D = 200mA
		-	0.45	0.8		V_{GS} = 2.5V, I_D = 200mA
		-	0.6	1.0		V_{GS} = 1.8V, I_D = 100mA
		-	0.7	1.6		V_{GS} = 1.5V, I_D = 50mA
Forward Transfer Admittance	$\|Y_{fs}\|$	-	1.4	-	S	V_{DS} = 3V, I_D = 200mA
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 500mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	37.0	-	pF	V_{DS} =16V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	5.7	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	4.2	-	pF	
Gate Resistance	R_g	-	68	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	-	0.5	-	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	-	0.07	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.1	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	4.06	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_G = 10Ω, I_D = 200mA
Turn-On Rise Time	t_R	-	7.28	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	13.74	-	ns	
Turn-Off Fall Time	t_F	-	10.54	-	ns	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

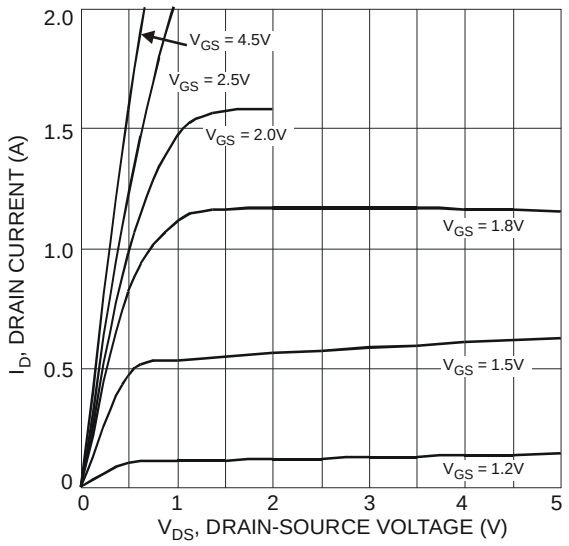


Fig. 1 Typical Output Characteristics

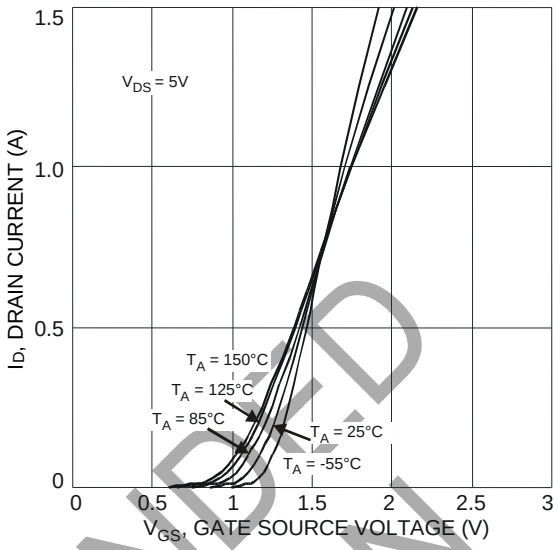


Fig. 2 Typical Transfer Characteristics

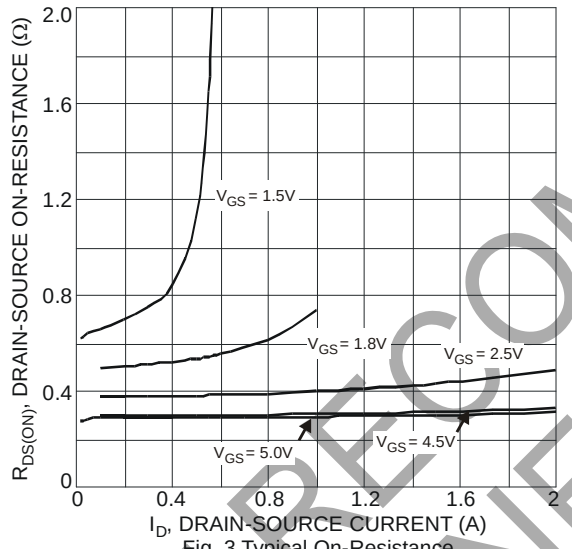


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

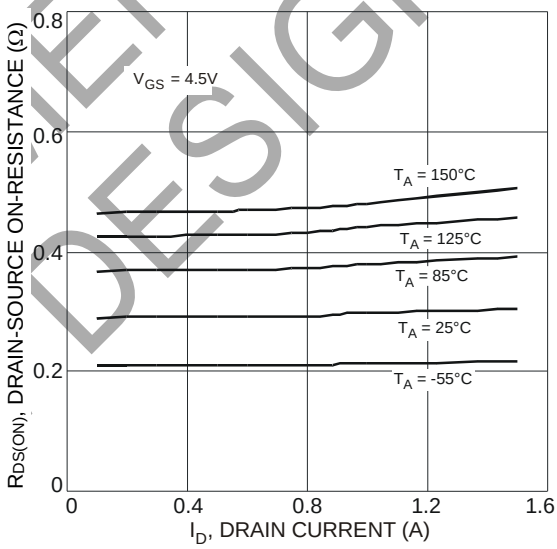


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

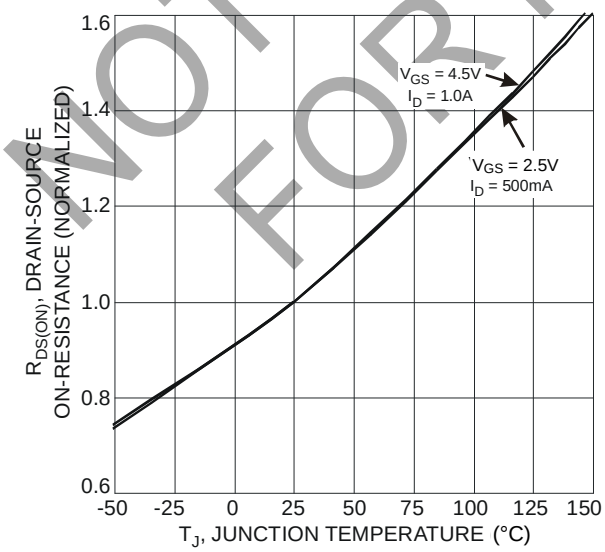


Fig. 5 On-Resistance Variation with Temperature

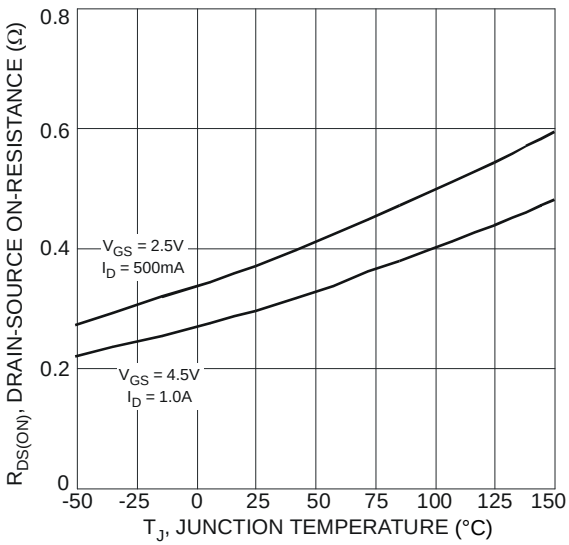


Fig. 6 On-Resistance Variation with Temperature

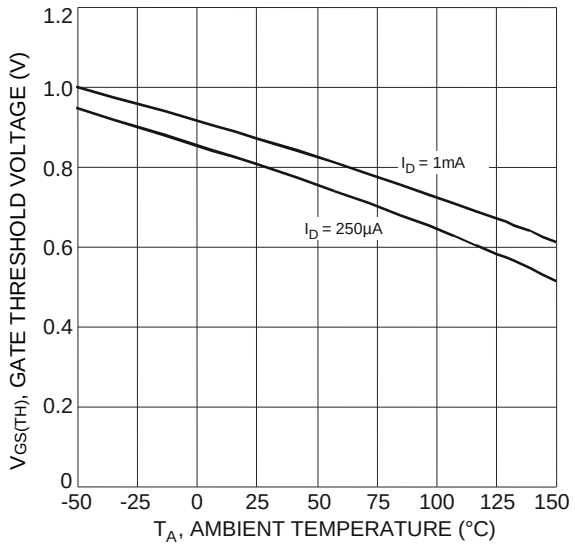


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

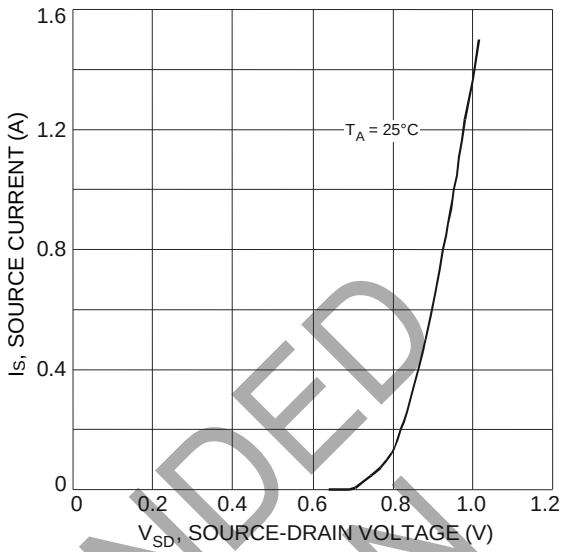


Fig. 8 Diode Forward Voltage vs. Current

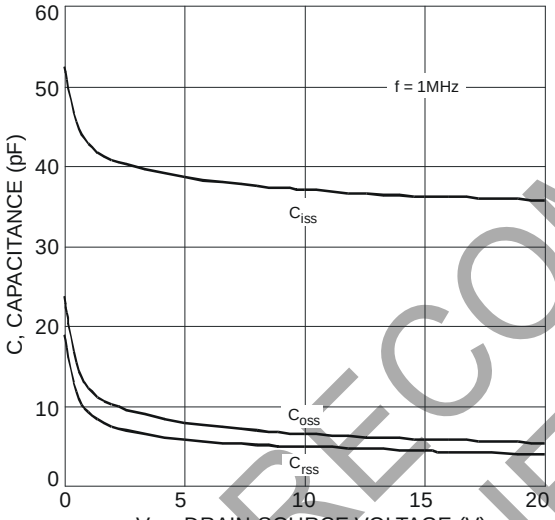


Fig. 9 Typical Capacitance

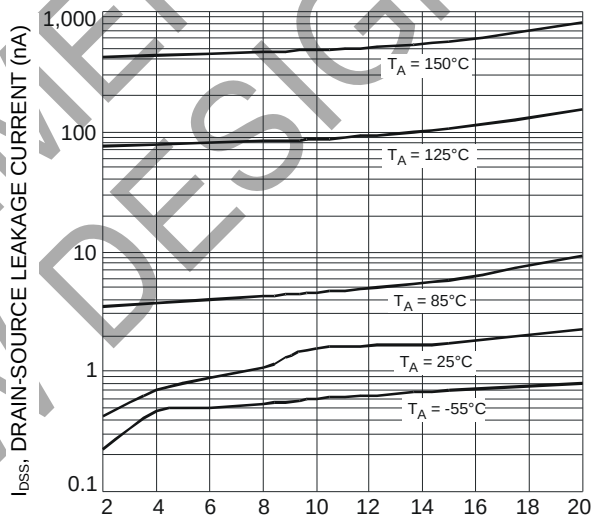


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

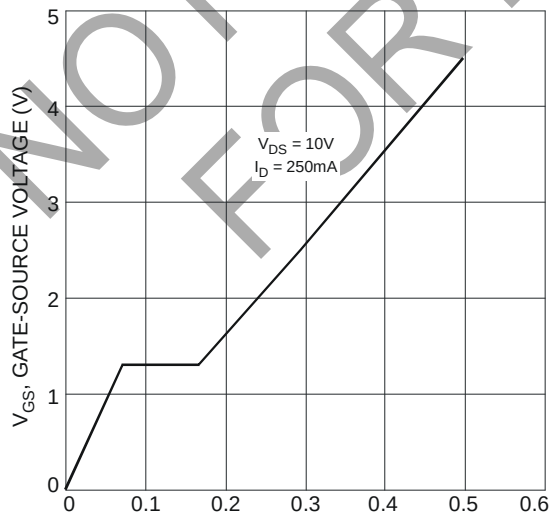


Fig. 11 Gate-Charge Characteristics

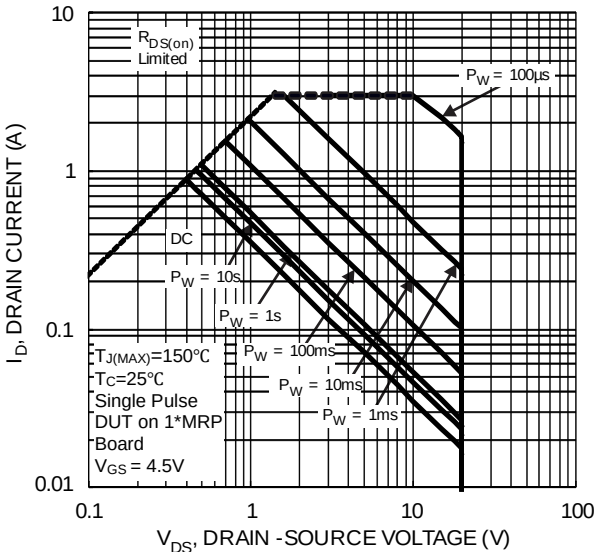


Fig. 12 SOA, Safe Operation Area

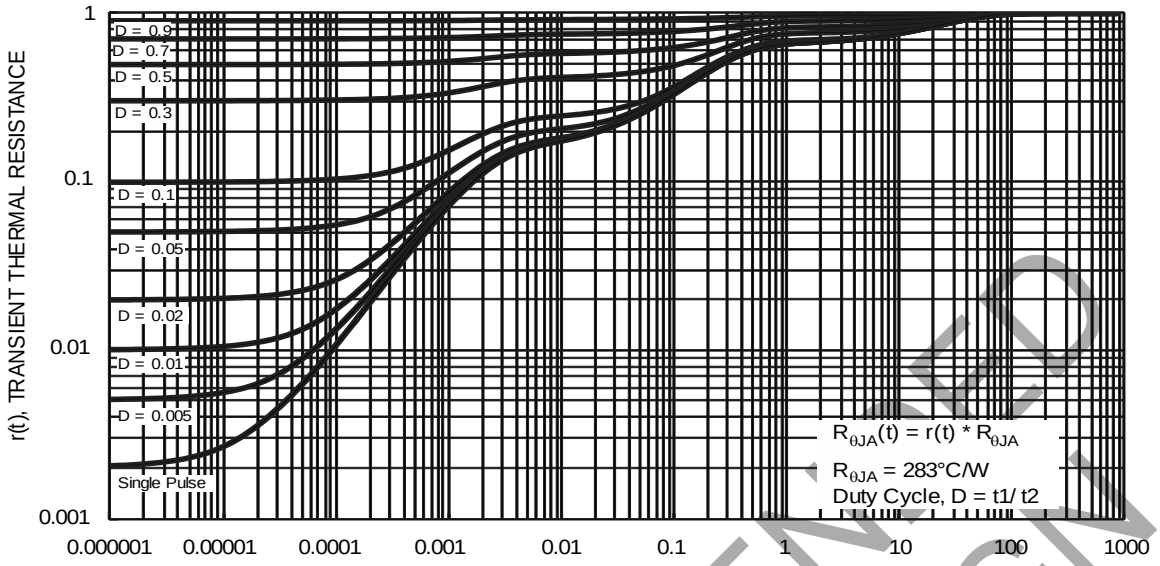
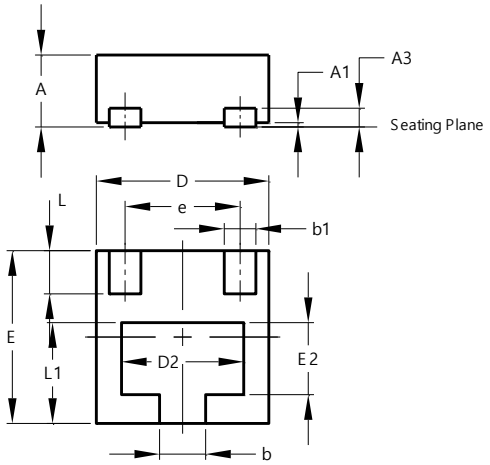


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1212-3 (Type C)

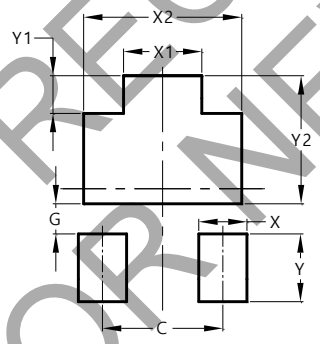


U-DFN1212-3 Type C			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
D2	0.75	0.95	0.85
e	-	-	0.80
E	1.15	1.25	1.20
E2	0.40	0.60	0.50
L	0.25	0.35	0.30
L1	0.65	0.75	0.70
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1212-3 (Type C)



Dimensions	Value (in mm)
C	0.800
G	0.200
X	0.320
X1	0.520
X2	1.050
Y	0.450
Y1	0.250
Y2	0.850

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